

ABSTRACT

An object of the present invention is to provide a
low-resistance n-type Group III nitride semiconductor
5 layered structure having excellent flatness and few pits.

The inventive n-type group III nitride semiconductor
layered structure comprises a substrate and, stacked on
the substrate, an n-type impurity concentration periodic
variation layer comprising an n-type impurity atom higher
10 concentration layer and an n-type impurity atom lower
concentration layer, said lower concentration layer being
stacked on said higher concentration layer.